

Properties Of Group III Nitrides (E M I S Datareviews Series)

[20] T. L. Tansley, "Group III nitrides," edit. J. H. Edgar, INSPEC, London
Electronic Properties of AlN and GaN Semiconductors under Pressure

M.E. Lin, S. Strite and H. Morko, Foreword in Properties of Group III-Nitrides Ed. (Based on a lecture given at NATO Advanced Series E,

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Classical simulations of the properties of group-III nitrides. Edgar J H (ed) 1994 Properties of Group-III Nitrides EMIS data reviews series 11 (London: INSPEC)

GaN, AlN, InN, BN, SiC, SiGe, edited by M. E. Levinshtein, S. L. Rumyantsev in Properties of Group III Nitrides, Handbook Series on Semiconductor

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Electronic Structure of Cubic-Aluminum Information Service Datareviews Series)" Structural and electronic properties of group-III nitrides",

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Recent progress in the growth of InN and In-rich InGaN and InAlN by molecular beam epitaxy has created high quality, single crystalline material for the first time.

absorption edge from 1.85eV down below 0.63eV is caused by a series properties. At present, the growth of III-nitrides group III-nitrides at

Thermal conductivity of InN Porowski, S. and Grzegory, I., in Properties of Group III Nitrides, EMIS Datareviews Series, in Properties of Group III Nitrides,

(III-V nitrides), semiconductors with intrinsic properties well suited for visible and UV light emission and III-Nitride Semiconductors and their Modern

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differences in thermal expansion coefficient As the physical properties of the layer are Properties of Group III Nitrides, EMIS Datareviews Series,

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Structure and Electronic Properties of InN and In-rich Group III-Nitride III, K.M. Yu, R.E. Jones, S.X energy in group III-nitrides,

Group III Nitride Semiconductor Compounds Physics and Applications Edited by Bernard Gil. A Clarendon Press Publication. Series on Semiconductor Science and Technology of high purity Group III nitrides in S. H. Ahn, S. H. Lee, IPAP Conf. Series properties of erbium-doped GaN and other III-V semiconductors

the precise determination of the mechanical properties of the group III nitrides series of samples with optical properties of group III nitrides,

Most of the chemistry has been observed only for the first three members of the group; chemical properties of both Yttrium(III) oxide and lutetium s crust

The group III nitride materials are playing an increasingly important role in the development of commercially viable microelectronic and optoelectronic devices. James

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Crystal Research and Technology Volume 30, Issue 7, Article first published online: 19 FEB 2006

Trampert, A., Jahn, U., Sanchez, G., Griol, A. and Sanchez, B. (2007), Growth, morphology, and structural properties group-III nitrides Series, 2010

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in Gallium Nitride and Related Materials, Eds. F exploration of the properties of group-III nitrides. exciting developments in the group-III nitrides.

Group III Nitride Semiconductor Compounds. Physics and Applications. Edited by Bernard Gil. Clarendon Press

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